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Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A display device including a main semiconductor layer formed on a substrate and a plurality of thin film transistors having the semiconductor layers, wherein:

the main semiconductor layer includes a first pseudo single crystal region and a second pseudo single crystal region which is formed at a position separated from the first pseudo single crystal region, and

out of the plurality of thin film transistors, two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as the characteristics of the transistors<sub>1</sub> are arranged in the same pseudo single crystal region.

2. (currently amended) A display device including a semiconductor layers layer formed on a substrate and having pseudo single crystal regions<sub>1</sub> and a plurality of thin film transistors arranged in the inside of the pseudo single crystal regions, wherein:

in the pseudo single crystal region, the semiconductor layer includes crystals which are grown in an elongate strip-like shape in ~~the~~ a direction parallel to the substrate, and

out of the plurality of thin film transistors, two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as the characteristics of the transistors<sub>1</sub> have the direction of ~~a~~ the length of gates of the respective thin film transistors arranged with an inclination of within  $\pm 20$  degree with

respect to the longitudinal direction of the strip-like grown crystals<sub>1</sub> and are arranged such that<sub>1</sub> when channel regions of the respective thin film transistors are imaginarily extended in parallel to the growth direction of the strip-like grown crystals, at least portions of the channel regions ~~are superpose~~ superposed on each other.

3. (currently amended) A display device according to claim 2, wherein a ~~rate extent of the superposition of the channel regions~~ is 50% or more.

4. (currently amended) A display device according to claim 3, wherein a ~~rate extent of the superposition of the channel regions~~ is 80% or more.

5. (currently amended) A display device including a semiconductor ~~layers~~ layer formed on a substrate and having pseudo single crystal regions<sub>1</sub> and a plurality of thin film transistors arranged in the inside of the pseudo single crystal regions, wherein:

in the pseudo single crystal region, the semiconductor layer includes crystals which are grown in an elongate strip-like shape in ~~the a~~ a direction parallel to the substrate, and

~~out of the plurality of thin film transistors, two or more thin film transistors<sub>1</sub>~~ which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> have the direction of ~~a~~ the length of gates of the respective thin film transistors arranged with an inclination of within  $\pm 20$  degree with respect to the longitudinal direction of the strip-like grown crystals<sub>1</sub> and are arranged such that the directions of currents which flow in the respective thin film transistors are aligned with each other.

6. (currently amended) A display device according to claim 1, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to

each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a differential pair of transistors which constitute a differential amplifying circuit.

7. (currently amended) A display device according to claim 1, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors of an active load circuit which constitutes a differential amplifying circuit.

8. (currently amended) A display device according to claim 1, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors of an active load circuit which constitutes a differential amplifying circuit and a transistor having a gate thereof to which an output voltage of the active load circuit is applied.

9. (currently amended) A display device according to claim 1, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors which constitute a current mirror circuit.

10. (currently amended) A display device according to claim 1, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are connected in parallel to each other<sub>1</sub> thus equivalently constituting one transistor.

11. (currently amended) A display device according to claim 2, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a differential pair of transistors which constitute a differential amplifying circuit.

12. (currently amended) A display device according to claim 2, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors of an active load circuit which constitutes a differential amplifying circuit.

13. (currently amended) A display device according to claim 2, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors of an active load circuit which constitutes a differential amplifying circuit and a transistor having a gate thereof to which an output voltage of the active load circuit is applied.

14. (currently amended) A display device according to claim 2, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors which constitute a current mirror circuit.

15. (currently amended) A display device according to claim 2, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are connected in parallel to each other thus equivalently constituting one transistor.

16. (currently amended) A display device according to claim 5, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a differential pair of transistors which constitute a differential amplifying circuit.

17. (currently amended) A display device according to claim 5, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to

each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors of an active load circuit which constitutes a differential amplifying circuit.

18. (currently amended) A display device according to claim 5, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors of an active load circuit which constitutes a differential amplifying circuit and a transistor having a gate thereof to which an output voltage of the active load circuit is applied.

19. (currently amended) A display device according to claim 5, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are formed of a pair of transistors which constitute a current mirror circuit.

20. (currently amended) A display device according to claim 5, wherein two or more thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics of the transistors<sub>1</sub> are connected in parallel to each other thus equivalently constituting one transistor.